

3. (amended) A dry etching method according to claim 2, wherein said fluorine-containing gas has a structure that the total number of fluorine atoms in elements constituting said gas molecule is four or less.

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4. (amended) A method of manufacturing a semiconductor apparatus comprising the steps of:

laminating upwards a polycrystal silicon film or an amorphous silicon film, a tungsten nitride film or a titanium nitride film, and a tungsten film on a silicon substrate; and

dry-etching said tungsten nitride film or said titanium nitride film and said tungsten film with mixed gas containing fluorine-containing gas that includes a compound having fluorine and carbon in a molecule, chlorine or hydrogen bromide, oxygen, and nitrogen so that a gate electrode is formed.

X 7
6. (amended) A method of manufacturing a semiconductor apparatus according to claim 4, wherein a mask is formed by silicon oxide or silicon nitride, and said gate electrode is formed by dry etching using said mask.

X 2
7. (amended) A method of manufacturing a semiconductor apparatus according to claim 4, said fluorine-containing gas has a structure that a ratio of fluorine atoms with respect to elements of the gas molecule except for fluorine is four or less when the composition of the fluorine molecule is M_xF_y , $y/x \leq 4$ where M is an element except for fluorine atom and F is fluorine.

8. (amended) A method of manufacturing a semiconductor apparatus according to claim 7, wherein said fluorine-containing gas has a structure that the total number of